3A, 24V, 500kHz Synchronous Step-Down Converter

General Description

The RT8299A is a high efficiency, monolithic synchronous step-down DC/DC converter with internal power MOSFETs. It achieves 3A of continuous output current over a wide input supply range from 3V to 24V with excellent load and line regulation. Current mode operation provides fast transient response and eases loop stabilization. Cycleby-cycle current limit provides protection against shorted outputs and soft-start eliminates input current surge during start-up. Thermal shutdown provides reliable, fault tolerant operation. The low current shutdown mode provides output disconnection, enabling easy power management in battery powered systems.

Ordering Information

RT8299A

Package Type
 SP : SOP-8 (Exposed Pad-Option 1)
 QW: WDFN-10L 3x3 (W-Type)

Lead Plating System

Z : ECO (Ecological Element with Halogen Free and Pb free)

Note :

Richtek products are :

- RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- Suitable for use in SnPb or Pb-free soldering processes.

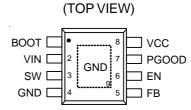
Features

- 3V to 24V Input Voltage Range
- 3A Output Current
- Internal N-MOSFETs
- Current Mode Control
- Fixed Frequency Operation : 500kHz
- Output Adjustable from 0.8V to 15V
- Up to 95% Efficiency
- Stable with Low ESR Ceramic Output Capacitors
- Cycle-by-Cycle Over Current Protection
- Input Under Voltage Lockout
- Output Under Voltage Protection
- Thermal Shutdown Protection
- SOP-8 (Exposed Pad) and 10-Lead WDFN Packages
- RoHS Compliant and Halogen Free

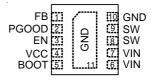
Applications

- Industrial and Commercial Low Power Systems
- Computer Peripherals
- LCD Monitors and TVs
- Green Electronics/Appliances
- Point of Load Regulation for High Performance DSPs, FPGAs, and ASICs

Pin Configurations



SOP-8 (Exposed Pad)



WDFN-10L 3x3

RT8299A



Marking Information

RT8299AZSP

RT8299A ZSPYMDNN RT8299AZSP : Product Number YMDNN : Date Code

RT8299AZQW



83 : Product Code YMDNN : Date Code

Typical Application Circuit

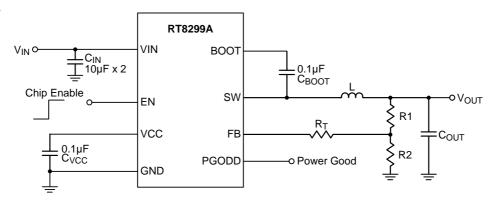


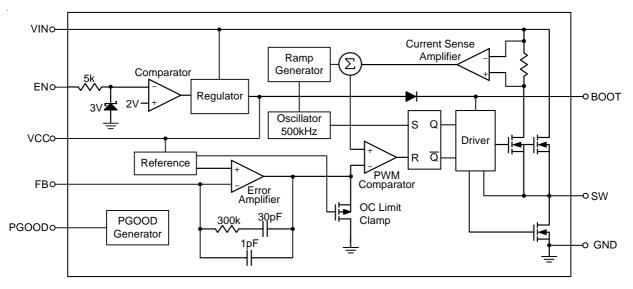
Table 1. Recommended Component Selection

V _{OUT} (V)	R1 (k Ω)	R2 (k Ω)	R_T (k Ω)	L (μ H)	Coυτ (μ F)
1.2	15	30	50	2	22 x 2
2.5	25.5	12	40	3.6	22 x 2
3.3	16	5.1	30	4.7	22 x 2
5	27	5.1	18	6.8	22 x 2

Functional Pin Description

Pin No.			
SOP-8 (Exposed Pad)	WDFN-10L 3x3	Pin Name	Pin Function
1	5	воот	Bootstrap for High Side Gate Driver. Connect a $0.1\mu F$ or greater ceramic capacitor from BOOT to SW pin.
2	6, 7	VIN	Supply Input Voltage. Must bypass with a suitably large ceramic capacitor.
3	8, 9	SW	Switch Node. Connect to external LC filter.
4, 9 (Exposed Pad)	10, 11 (Exposed Pad)	GND	Ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.
5	1	FB	Feedback Input. This pin is connected to the converter output. It is used to set the output of the converter to regulate to the desired value via an external resistive divider. The feedback reference voltage is 0.8V typically.
6	3	EN	Enable Input. A logic high enables the converter; a logic low forces the RT8299A into shutdown mode, reducing the supply current to less than 3μ A. Attach this pin to VIN with a $100k\Omega$ pull up resistor for automatic startup.
7	2	PGOOD	Power Good Indicator with Open Drain. A $100k\Omega$ pull-high resistor is needed. The output of this pin is pulled to low when the FB is lower than 0.75V; otherwise it is high impedance.
8	4	VCC	Bias Supply.

Function Block Diagram





Absolute Maximum Ratings (Note 1)

Supply Input Voltage, V _{IN}	- –0.3 to 26V
• Switching Voltage, SW	-0.3 to (V _{IN} + 0.3V)
< 10ns	-5V to 30V
BOOT to SW	- –0.3 to 6V
All Other Pins	- –0.3 to 6V
• Power Dissipation, $P_D @ T_A = 25^{\circ}C$	
SOP-8 (Exposed Pad)	- 1.333W
WDFN-10L 3x3	- 1.429W
Package Thermal Resistance (Note 2)	
SOP-8 (Exposed Pad), θ_{JA}	- 75°C/W
SOP-8 (Exposed Pad), θ_{JC}	- 15°C/W
WDFN-10L 3x3, θ _{JA}	- 70°C/W
WDFN-10L 3x3, θ_{JC}	- 8.2°C/W
Lead Temperature (Soldering, 10 sec.)	- 260°C
Junction Temperature	- 150°C
Storage Temperature Range	65°C to 150°C
ESD Susceptibility (Note 3)	
HBM (Human Body Mode)	· 2kV
MM (Machine Mode)	- 200V

Recommended Operating Conditions (Note 4)

Supply Voltage, V _{IN}	- 3V to 24V
Junction Temperature Range	- –40°C to 125°C
Ambient Temperature Range	40°C to 85°C

Electrical Characteristics

(V_{IN}\, = 12V, T_A = 25°C, unless otherwise specified)

Parameter		Symbol	Test Conditions	Min	Тур	Max	Unit
Shutdown Current		ISHDN	$V_{EN} = 0V$			3	μΑ
Supply Current			$V_{EN} = 3V, V_{FB} = 1V$		1		mA
Upper Switch On R	esistance				100		mΩ
Lower Switch On R	esistance				100		mΩ
Switch Leakage			$V_{EN} = 0V, V_{SW} = 0V \text{ or } 12V$		0	10	μΑ
Current Limit		I _{LIM}	$V_{BOOT} - V_{SW} = 4.8V$		5.5		Α
Oscillator Frequency		fosc	V _{FB} = 0.75V	425	500	575	kHz
Short Circuit Frequ	Short Circuit Frequency		V _{FB} = 0V		150		kHz
Maximum Duty Cyc	cle	D _{MAX}	V _{FB} = 0.8V		93		%
Minimum On-Time		ton			100		ns
Feedback Voltage		VFB	$3V \le V_{IN} \le 24V$	788	800	812	mV
EN Input Logic-High		Vih		2		5.5	v
Threshold Voltage	Logic-Low	VIL				0.4	V
Under Voltage Lockout Threshold		Vuvlo	V _{IN} Rising		2.8		V

RT8299A

Parameter Symbol Test Conditions		Min	Тур	Max	Unit	
Under Voltage Lockout Threshold Hysteresis	ΔVυνιο			300		mV
Power Good Threshold		VOUT Rising, with Respect to V_{FB}		90		%
		VOUT Falling, with Respect to V_{FB}		70		70
VCC Regulator				5		V
VCC Load Regulation		I _{CC} = 5mA		5		%
Soft-Start Period	tss			2		ms
Thermal Shutdown	T _{SD}			150		°C

Note 1. Stresses beyond those listed "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

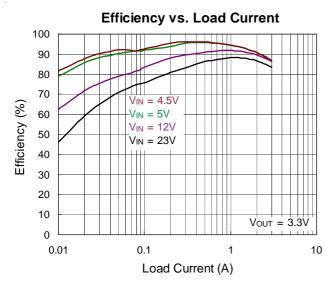
Note 3. Devices are ESD sensitive. Handling precaution is recommended.

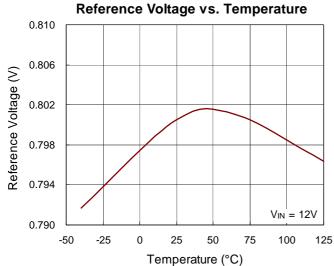
Note 4. The device is not guaranteed to function outside its operating conditions.

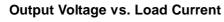
Note 2. θ_{JA} is measured at $T_A = 25^{\circ}C$ on a high effective thermal conductivity four-layer test board per JEDEC 51-7. θ_{JC} is measured at the exposed pad of the package.



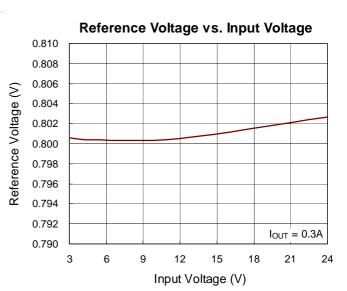
Typical Operating Characteristics



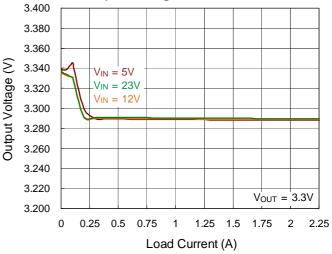




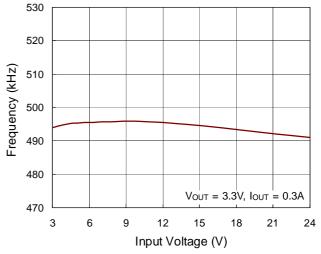




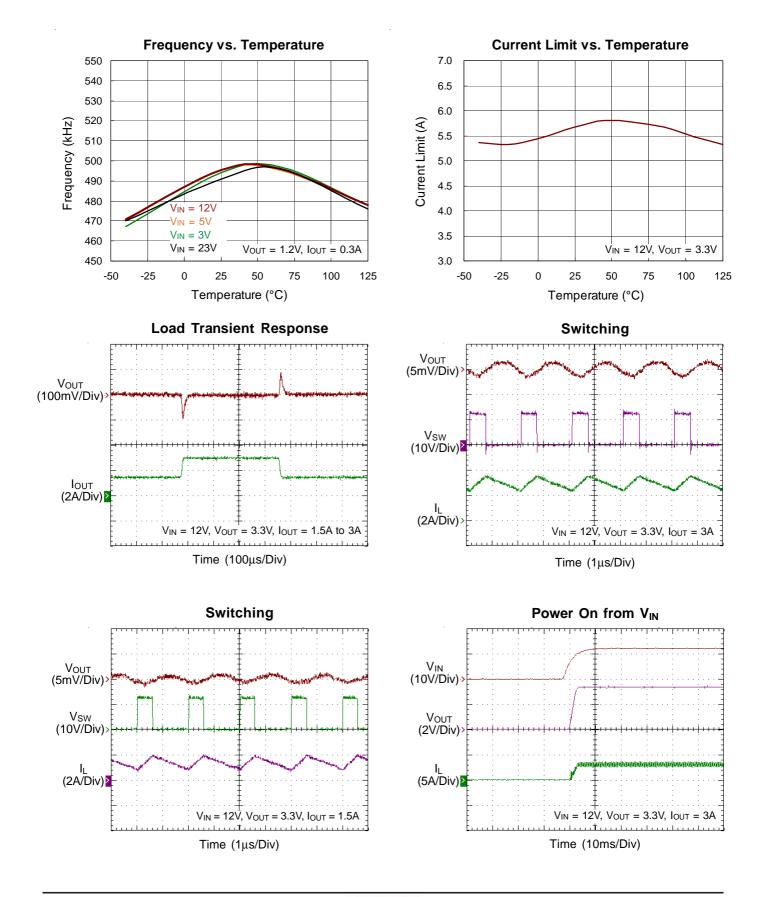
Output Voltage vs. Load Current



Frequency vs. Input Voltage

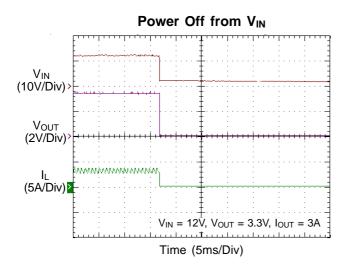


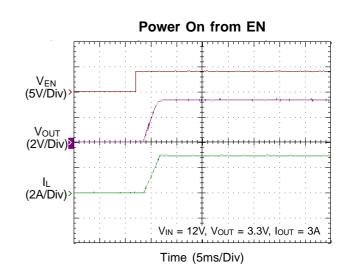
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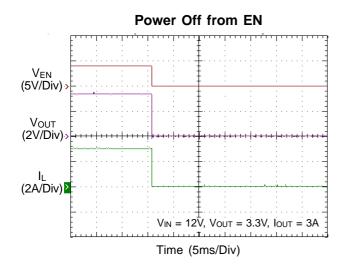


RT8299A









Application Information

The RT8299A is a synchronous high voltage buck converter that can support the input voltage range from 3V to 24V and the output current can be up to 3A.

Output Voltage Setting

The resistive divider allows the FB pin to sense the output voltage as shown in Figure 1.

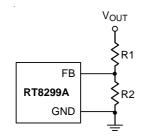


Figure 1. Output Voltage Setting

The output voltage is set by an external resistive voltage divider according to the following equation :

$$V_{OUT} = V_{FB} \left(1 + \frac{R1}{R2} \right)$$

where V_{FB} is the feedback reference voltage (0.8V typ.).

External Bootstrap Diode

Connect a 100nF low ESR ceramic capacitor between the BOOT pin and SW pin. This capacitor provides the gate driver voltage for the high side MOSFET.

It is recommended to add an external bootstrap diode between an external 5V and BOOT pin for efficiency improvement when input voltage is lower than 5.5V or duty ratio is higher than 65% .The bootstrap diode can be a low cost one such as IN4148 or BAT54. The external 5V can be a 5V fixed input from system or a 5V output of the RT8299A. Note that the external boot voltage must be lower than 5.5V

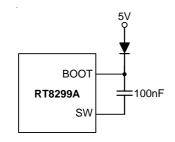


Figure 2. External Bootstrap Diode

Chip Enable Operation

The EN pin is the chip enable input. Pulling the EN pin low (<0.4V) will shutdown the device. During shutdown mode, the RT8299A guiescent current drops to lower than 3μ A. Driving the EN pin high (>2V, < 5.5V) will turn on the device again. For external timing control (e.g.RC), the EN pin can also be externally pulled high by adding a REN* resistor and CEN* capacitor from the VIN pin (see Figure 5).

An external MOSFET can be added to implement digital control on the EN pin when no system voltage above 2.5V is available, as shown in Figure 3. In this case, a $100k\Omega$ pull-up resistor, R_{EN}, is connected between VIN pin and the EN pin. MOSFET Q1 will be under logic control to pull down the EN pin.

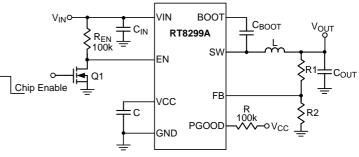


Figure 3. Enable Control Circuit for Logic Control with Low Voltage

To prevent enabling circuit when V_{IN} is smaller than the VOUT target value, a resistive voltage divider can be placed between the input voltage and ground and connected to the EN pin to adjust IC lockout threshold, as shown in Figure 4. For example, if an 8V output voltage is regulated from a 12V input voltage, the resistor REN2 can be selected to set input lockout threshold larger than 8V.

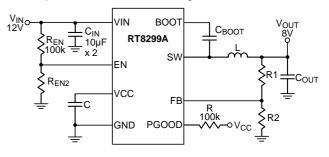


Figure 4. The Resistors can be Selected to Set IC Lockout Threshold

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DS8299A-01	October 2013		www.richtek.com

Under Voltage Protection

For the RT8299A, it provides Hiccup Mode Under Voltage Protection (UVP). When the FB voltage drops below half of the feedback reference voltage, V_{FB} , the UVP function will be triggered and the RT8299A will shut down for a period of time and then recover automatically. The Hiccup Mode UVP can reduce input current in short-circuit conditions.

Inductor Selection

The inductor value and operating frequency determine the ripple current according to a specific input and output voltage. The ripple current ΔI_L increases with higher V_{IN} and decreases with higher inductance.

$$\Delta I_{L} = \left[\frac{V_{OUT}}{f \times L}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN}}\right]$$

Having a lower ripple current reduces not only the ESR losses in the output capacitors but also the output voltage ripple. High frequency with small ripple current can achieve highest efficiency operation. However, it requires a large inductor to achieve this goal.

For the ripple current selection, the value of $\Delta I_L = 0.24(I_{MAX})$ will be a reasonable starting point. The largest ripple current occurs at the highest V_{IN}. To guarantee that the ripple current stays below the specified maximum, the inductor value should be chosen according to the following equation :

$$L = \left[\frac{V_{OUT}}{f \times \Delta I_{L(MAX)}}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN(MAX)}}\right]$$

The inductor's current rating (caused a 40°C temperature rising from 25°C ambient) should be greater than the maximum load current and its saturation current should be greater than the short circuit peak current limit. Please see Table 2 for the inductor selection reference.

Table 2. Suggested Inductors for Typical Application Circuit

Component Supplier	Series	Dimensions (mm)				
TDK	VLF10045	10 x 9.7 x 4.5				
TDK	SLF12565	12.5 x 12.5 x 6.5				
TAIYO YUDEN	NR 8040	8 x 8 x 4				

\textbf{C}_{IN} and \textbf{C}_{OUT} Selection

The input capacitance, C_{IN} , is needed to filter the trapezoidal current at the source of the high side MOSFET. To prevent large ripple current, a low ESR input capacitor sized for the maximum RMS current should be used. The RMS current is given by :

$$I_{RMS} = I_{OUT(MAX)} \frac{V_{OUT}}{V_{IN}} \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT} / 2$. This simple worst case condition is commonly used for design because even significant deviations do not offer much relief.

Choose a capacitor rated at a higher temperature than required. Several capacitors may also be paralleled to meet size or height requirements in the design.

For the input capacitor, two $10\mu F$ low ESR ceramic capacitors are recommended.

The selection of C_{OUT} is determined by the required ESR to minimize voltage ripple.

Moreover, the amount of bulk capacitance is also a key for C_{OUT} selection to ensure that the control loop is stable. Loop stability can be checked by viewing the load transient response as described in a later section.

The output ripple, ΔV_{OUT} , is determined by :

$$\Delta V_{OUT} \leq \Delta I_L \left[\text{ESR} + \frac{1}{8 f C_{OUT}} \right]$$

The output ripple will be highest at the maximum input voltage since ΔI_L increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirement. Dry tantalum, special polymer, aluminum electrolytic and ceramic capacitors are all available in surface mount packages. Special polymer capacitors offer very low ESR value. However, it provides lower capacitance density than other types. Although Tantalum capacitors have the highest capacitance density, it is important to only use types that pass the surge test for use in switching power supplies. Aluminum electrolytic capacitors have significantly higher ESR. However, it can be used in cost-sensitive applications for ripple current rating and long term reliability considerations. Ceramic capacitors have excellent low

ESR characteristics but can have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can also lead to significant ringing.

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. However, care must be taken when these capacitors are used at input and output. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, V_{IN} . At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at V_{IN} large enough to damage the part.

Checking Transient Response

The regulator loop response can be checked by looking at the load transient response. Switching regulators take several cycles to respond to a step in load current. When a load step occurs, V_{OUT} immediately shifts by an amount equal to ΔI_{LOAD} (ESR) also begins to charge or discharge C_{OUT} generating a feedback error signal for the regulator to return V_{OUT} to its steady-state value. During this recovery time, V_{OUT} can be monitored for overshoot or ringing that would indicate a stability problem.

EMI Consideration

Since parasitic inductance and capacitance effects in PCB circuitry would cause a spike voltage on SW pin when high side MOSFET is turned-on/off, this spike voltage on SW may impact on EMI performance in the system. In order to enhance EMI performance, there are two methods to suppress the spike voltage. One is to place an R-C snubber between SW and GND and make them as close as possible to the SW pin (see Figure 5). Another method is adding a resistor R_{BOOT}* in series with the bootstrap capacitor, CBOOT. But this method will decrease the driving capability to the high side MOSFET. It is strongly recommended to reserve the R-C snubber during PCB layout for EMI improvement. Moreover, reducing the SW trace area and keeping the main power in a small loop will be helpful on EMI performance. For detailed PCB layout guide, please refer to the section of Layout Consideration.

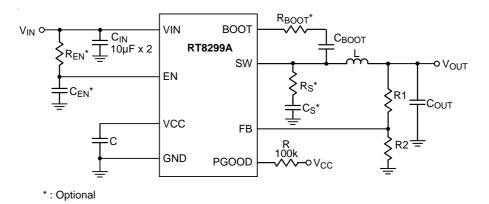


Figure 5. Reference Circuit with Snubber and Enable Timing Control

RT8299A

Thermal Considerations

For continuous operation, do not exceed the maximum operation junction temperature 125°C. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junction to ambient. The maximum power dissipation can be calculated by following formula :

 $\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = (\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}) / \theta_{\mathsf{J}\mathsf{A}}$

Where $T_{J(MAX)}$ is the maximum operation junction temperature, T_A is the ambient temperature and the θ_{JA} is the junction to ambient thermal resistance.

For recommended operating condition specifications of the RT8299A, the maximum junction temperature is 125°C and T_A is the ambient temperature. The junction to ambient thermal resistance, θ_{JA} , is layout dependent. For SOP-8 (Exposed Pad) packages, the thermal resistance, θ_{JA} , is 75°C/W on a standard JEDEC 51-7 four-layer thermal test board. For WDFN-10L 3x3 packages, the thermal resistance, θ_{JA} , is 70°C/W on a standard JEDEC 51-7 four-layer thermal resistance, θ_{JA} , is 70°C/W on a standard JEDEC 51-7 four-layer thermal test board. The maximum power dissipation at T_A = 25°C can be calculated by the following formulas :

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (75^{\circ}C/W) = 1.333W$ for

SOP-8 (Exposed Pad) package

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (70^{\circ}C/W) = 1.429W$ for

WDFN-10L 3x3 package

The maximum power dissipation depends on the operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance, θ_{JA} . For the RT8299A package, the derating curves in Figure 6 allow the designer to see the effect of rising ambient temperature on the maximum power dissipation.

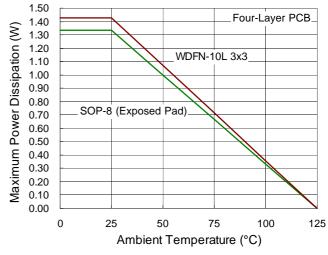


Figure 6. Derating Curves for RT8299A Packages

Layout Consideration

Follow the PCB layout guidelines for optimal performance of the RT8299A.

- Keep the traces of the main current paths as short and wide as possible.
- Put the input capacitor as close as possible to the device pins (VIN and GND).
- LX node is with high frequency voltage swing and should be kept at small area. Keep analog components away from the LX node to prevent stray capacitive noise pickup.
- Connect feedback network behind the output capacitors. Keep the loop area small. Place the feedback components near the RT8299A.
- Connect all analog grounds to a common node and then connect the common node to the power ground behind the output capacitors.
- An example of PCB layout guide is shown in Figure 7 for reference.





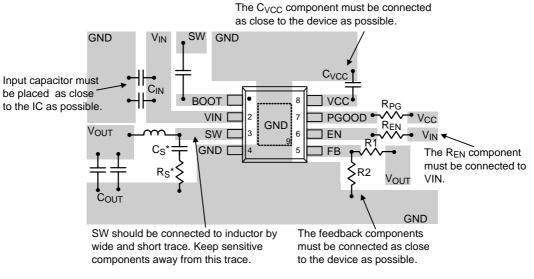
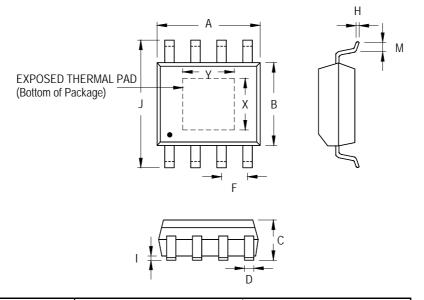


Figure 7. PCB Layout Guide

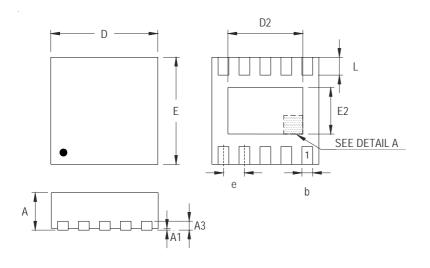


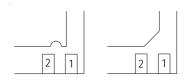
Outline Dimension



Symbol		Dimensions I	n Millimeters	Dimension	s In Inches	
		Min	Max	Min	Max	
А		4.801	5.004	0.189	0.197	
В		3.810	4.000	0.150	0.157	
С		1.346	1.753	0.053	0.069	
D		0.330	0.510	0.013	0.020	
F		1.194	1.346	0.047	0.053	
Н		0.170	0.254	0.007	0.010	
I		0.000	0.152	0.000	0.006	
J		5.791	6.200	0.228	0.244	
М		0.406	1.270	0.016	0.050	
Option 1	Х	2.000	2.300	0.079	0.091	
Option 1	Y	2.000	2.300	0.079	0.091	
Option 2	Х	2.100	2.500	0.083	0.098	
Option 2	Y	3.000	3.500	0.118	0.138	

8-Lead SOP (Exposed Pad) Plastic Package





DETAIL A Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions I	n Millimeters	Dimensions In Inche	
	Min	Max	Min	Max
А	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.180	0.300	0.007	0.012
D	2.950	3.050	0.116	0.120
D2	2.300	2.650	0.091	0.104
E	2.950	3.050	0.116	0.120
E2	1.500	1.750	0.059	0.069
е	0.500		0.0)20
L	0.350	0.450	0.014	0.018

W-Type 10L DFN 3x3 Package

Richtek Technology Corporation

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